



SDI FINAL EVALUATION FORM 1.1

PART 1:

Journal Name:	Physical Science International Journal
Manuscript Number:	2015_PSIJ_17567
Title of the Manuscript:	Modeling and Simulation of High Blocking Voltage in 4H Silicon Carbide Bipolar Junction Transistors
Type of Article	

PART 2:

FINAL EVALUATOR'S comments on revised paper (if any)	Authors' response to final evaluator's comments
I accept paper in its current form.	

Reviewer Details:

Name:	Anonymous
Department, University & Country	Ege University, Turkey